

Title (en)
HIGH-TEMPERATURE-RESISTANT COMPONENT STRUCTURE FREE OF SOLDERING AGENT, AND METHOD FOR ELECTRICAL CONTACT-
CONNECTION

Title (de)
HOCHTEMPERATURBESTÄNDIGE LÖTMITTELFREIE BAUELEMENTSTRUKTUR UND VERFAHREN ZUM ELEKTRISCHEN KONTAKTIEREN

Title (fr)
STRUCTURE DE COMPOSANT EXEMPT DE MÉTAL D'APPORT ET RÉSISTANT AUX HAUTES TEMPÉRATURES ET PROCÉDÉ DE MISE EN
CONTACT ÉLECTRIQUE

Publication
EP 2382654 A1 20111102 (DE)

Application
EP 09799060 A 20091203

Priority
• EP 2009066336 W 20091203
• DE 102008055138 A 20081223

Abstract (en)
[origin: WO2010072534A1] The invention relates to a component structure, comprising: an electrical or electronic component (10) having an upper contact area (12) on a top side of the component and a lower contact area (14) on an opposite underside of the component; an upper metal layer (40) and a lower metal layer (42); and an upper porous interlayer (20) and a lower porous interlayer (22). The upper interlayer mechanically and electrically conductively connects the upper metal layer to the upper contact area, and the lower interlayer mechanically and electrically conductively connects the lower metal layer to the lower contact area.

IPC 8 full level
H01L 21/60 (2006.01)

CPC (source: EP)
H01L 24/33 (2013.01); **H01L 24/75** (2013.01); **H01L 24/83** (2013.01); **H01L 2224/04026** (2013.01); **H01L 2224/29324** (2013.01); **H01L 2224/29339** (2013.01); **H01L 2224/29344** (2013.01); **H01L 2224/29347** (2013.01); **H01L 2224/83099** (2013.01); **H01L 2224/83101** (2013.01); **H01L 2224/83801** (2013.01); **H01L 2224/8384** (2013.01); **H01L 2924/01005** (2013.01); **H01L 2924/01006** (2013.01); **H01L 2924/01013** (2013.01); **H01L 2924/01015** (2013.01); **H01L 2924/01029** (2013.01); **H01L 2924/01046** (2013.01); **H01L 2924/01047** (2013.01); **H01L 2924/01058** (2013.01); **H01L 2924/01078** (2013.01); **H01L 2924/01079** (2013.01); **H01L 2924/01082** (2013.01); **H01L 2924/014** (2013.01); **H01L 2924/13091** (2013.01)

Citation (search report)
See references of WO 2010072534A1

Citation (examination)
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• "CHAPTER 4: Eigenschaften und Charakterisierung von NTV-Verbindungen ED - MERTENS CHRISTIAN", 1 January 2004, DIE NIEDERTEMPERATUR-VERBINDUNGSTECHNIK DER LEISTUNGSELEKTRONIK (BOOK SERIES: FORTSCHRITT-BERICHTS VDI); [FORTSCHRITT-BERICHTS VDI : REIHE 21, ELEKTROTECHNIK ; 365], VDI VERLAG, DÜSSELDORF, GERMANY, PAGE(S) 73 - 115, ISBN: 978-3-18-336521-0, XP001526268

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)
DE 102008055138 A1 20100701; EP 2382654 A1 20111102; WO 2010072534 A1 20100701

DOCDB simple family (application)
DE 102008055138 A 20081223; EP 09799060 A 20091203; EP 2009066336 W 20091203